

Bias-temperature stability test for metal-oxide, semiconductor, field-effect transistors (MOSFET)

The European Standard EN 62373:2006 has the status of a British Standard

ICS 31.080

National foreword

This British Standard was published by BSI. It is the UK implementation of EN 62373:2006. It is identical with IEC 62373:2006.

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A list of organizations represented on EPL/47 can be obtained on request to its secretary.

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**Bias-temperature stability test for
metal-oxide, semiconductor, field-effect transistors
(MOSFET)
(IEC 62373:2006)**

Essai de stabilité de température en
polarisation pour transistors à effet de
champ métal-oxyde-semiconducteur
(MOSFET)
(CEI 62373:2006)

Stabilitätsprüfung unter
Temperatur-Spannungs-Beanspruchung
für Feldeffekttransistoren mit
Metalloxid-Halbleiter (MOSFET)
(IEC 62373:2006)

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CENELEC

European Committee for Electrotechnical Standardization
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Europäisches Komitee für Elektrotechnische Normung

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Foreword

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Endorsement notice

The text of the International Standard IEC 62373:2006 was approved by CENELEC as a European Standard without any modification.

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